

# NSS40400CF8T1G

## 40 V, 7 A, Low $V_{CE(sat)}$ PNP Transistor

ON Semiconductor's e<sup>2</sup>PowerEdge family of low  $V_{CE(sat)}$  transistors are miniature surface mount devices featuring ultra low saturation voltage ( $V_{CE(sat)}$ ) and high current gain capability. These are designed for use in low voltage, high speed switching applications where affordable efficient energy control is important.

Typical application are DC-DC converters and power management in portable and battery powered products such as cellular and cordless phones, PDAs, computers, printers, digital cameras and MP3 players. Other applications are low voltage motor controls in mass storage products such as disc drives and tape drives. In the automotive industry they can be used in air bag deployment and in the instrument cluster. The high current gain allows e<sup>2</sup>PowerEdge devices to be driven directly from PMU's control outputs, and the Linear Gain (Beta) makes them ideal components in analog amplifiers.

### MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ )

| Rating                         | Symbol    | Max                        | Unit |
|--------------------------------|-----------|----------------------------|------|
| Collector-Emitter Voltage      | $V_{CEO}$ | -40                        | Vdc  |
| Collector-Base Voltage         | $V_{CBO}$ | -60                        | Vdc  |
| Emitter-Base Voltage           | $V_{EBO}$ | -5.0                       | Vdc  |
| Collector Current – Continuous | $I_C$     | -4.0                       | Adc  |
| Collector Current – Peak       | $I_{CM}$  | -7.0                       | A    |
| Electrostatic Discharge        | ESD       | HBM Class 3B<br>MM Class C |      |

### THERMAL CHARACTERISTICS

| Characteristic                                                                        | Symbol                                | Max            | Unit                       |
|---------------------------------------------------------------------------------------|---------------------------------------|----------------|----------------------------|
| Total Device Dissipation, $T_A = 25^\circ\text{C}$<br>Derate above $25^\circ\text{C}$ | $P_D$ (Note 1)                        | 650<br>5.2     | mW<br>mW/ $^\circ\text{C}$ |
| Thermal Resistance,<br>Junction-to-Ambient                                            | $R_{\theta JA}$ (Note 1)              | 192            | $^\circ\text{C}/\text{W}$  |
| Total Device Dissipation, $T_A = 25^\circ\text{C}$<br>Derate above $25^\circ\text{C}$ | $P_D$ (Note 2)                        | 1.57<br>12.7   | W<br>mW/ $^\circ\text{C}$  |
| Thermal Resistance,<br>Junction-to-Ambient                                            | $R_{\theta JA}$ (Note 2)              | 79             | $^\circ\text{C}/\text{W}$  |
| Thermal Resistance,<br>Junction-to-Lead #1                                            | $R_{\theta JL}$                       | 15             | $^\circ\text{C}/\text{W}$  |
| Total Device Dissipation<br>(Single Pulse < 10 sec)                                   | $P_{D\text{single}}$<br>(Notes 2 & 3) | 2.75           | W                          |
| Junction and Storage<br>Temperature Range                                             | $T_J, T_{stg}$                        | -55 to<br>+150 | $^\circ\text{C}$           |

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

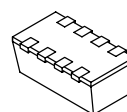
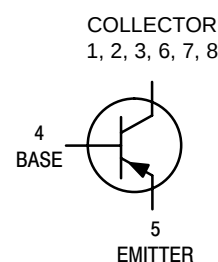
1. FR-4 @ 100 mm<sup>2</sup>, 2 oz copper traces.
2. FR-4 @ 500 mm<sup>2</sup>, 2 oz copper traces.
3. Thermal response.



ON Semiconductor®

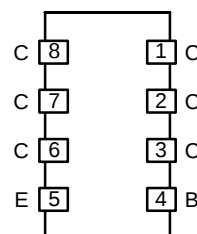
<http://onsemi.com>

**40 VOLTS**  
**7.0 AMPS**  
**PNP LOW  $V_{CE(sat)}$  TRANSISTOR**  
**EQUIVALENT  $R_{DS(on)}$  78 m $\Omega$**

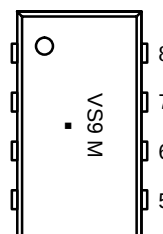


ChipFET™  
CASE 1206A  
STYLE 4

### PIN CONNECTIONS



### MARKING DIAGRAM



VS9 = Specific Device Code  
M = Month Code  
▪ = Pb-Free Package  
(Note: Microdot may be in either location)

### ORDERING INFORMATION

| Device         | Package              | Shipping†            |
|----------------|----------------------|----------------------|
| NSS40400CF8T1G | ChipFET<br>(Pb-Free) | 3000/<br>Tape & Reel |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# NSS40400CF8T1G

## ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted)

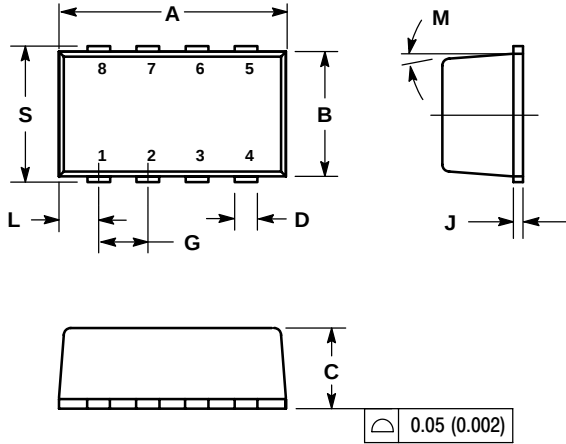
| Characteristic                                                                                                                                                                                                                                                                                                                         | Symbol               | Min                      | Typical                                        | Max                                         | Unit |
|----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|----------------------|--------------------------|------------------------------------------------|---------------------------------------------|------|
| <b>OFF CHARACTERISTICS</b>                                                                                                                                                                                                                                                                                                             |                      |                          |                                                |                                             |      |
| Collector – Emitter Breakdown Voltage<br>(I <sub>C</sub> = -10 mAdc, I <sub>B</sub> = 0)                                                                                                                                                                                                                                               | V <sub>(BR)CEO</sub> | -40                      |                                                | -                                           | Vdc  |
| Collector – Base Breakdown Voltage<br>(I <sub>C</sub> = -0.1 mAdc, I <sub>E</sub> = 0)                                                                                                                                                                                                                                                 | V <sub>(BR)CBO</sub> | -60                      | -                                              | -                                           | Vdc  |
| Emitter – Base Breakdown Voltage<br>(I <sub>E</sub> = -0.1 mAdc, I <sub>C</sub> = 0)                                                                                                                                                                                                                                                   | V <sub>(BR)EBO</sub> | -5.0                     | -                                              | -                                           | Vdc  |
| Collector Cutoff Current<br>(V <sub>CB</sub> = -60 Vdc, I <sub>E</sub> = 0)                                                                                                                                                                                                                                                            | I <sub>CBO</sub>     | -                        | -                                              | -0.1                                        | μAdc |
| Emitter Cutoff Current<br>(V <sub>EB</sub> = -6.0 Vdc)                                                                                                                                                                                                                                                                                 | I <sub>EBO</sub>     | -                        | -                                              | -0.1                                        | μAdc |
| <b>ON CHARACTERISTICS</b>                                                                                                                                                                                                                                                                                                              |                      |                          |                                                |                                             |      |
| DC Current Gain (Note 4)<br>(I <sub>C</sub> = -1.0 A, V <sub>CE</sub> = -2.0 V)<br>(I <sub>C</sub> = -1.5 A, V <sub>CE</sub> = -2.0 V)<br>(I <sub>C</sub> = -2.0 A, V <sub>CE</sub> = -2.0 V)<br>(I <sub>C</sub> = -3.0 A, V <sub>CE</sub> = -2.0 V)                                                                                   | h <sub>FE</sub>      | 100<br>100<br>100<br>100 | 220<br>220<br>220<br>220                       | -<br>400<br>-<br>-                          |      |
| Collector – Emitter Saturation Voltage (Note 4)<br>(I <sub>C</sub> = -0.1 A, I <sub>B</sub> = -0.010 A)<br>(I <sub>C</sub> = -1.0 A, I <sub>B</sub> = -0.010 A)<br>(I <sub>C</sub> = -2.0 A, I <sub>B</sub> = -0.02 A)<br>(I <sub>C</sub> = -3.0 A, I <sub>B</sub> = -0.030 A)<br>(I <sub>C</sub> = -4.0 A, I <sub>B</sub> = -0.400 A) | V <sub>CE(sat)</sub> | -<br>-<br>-<br>-<br>-    | -0.010<br>-0.127<br>-0.240<br>-0.250<br>-0.180 | -0.015<br>-0.145<br>-0.30<br>-0.45<br>-0.35 | V    |
| Base – Emitter Saturation Voltage (Note 4)<br>(I <sub>C</sub> = -1.0 A, I <sub>B</sub> = -0.01 A)                                                                                                                                                                                                                                      | V <sub>BE(sat)</sub> | -                        | -0.82                                          | -0.85                                       | V    |
| Base – Emitter Turn-on Voltage (Note 4)<br>(I <sub>C</sub> = -2.0 A, V <sub>CE</sub> = -3.0 V)                                                                                                                                                                                                                                         | V <sub>BE(on)</sub>  | -                        | -0.82                                          | -0.875                                      | V    |
| Cutoff Frequency<br>(I <sub>C</sub> = -100 mA, V <sub>CE</sub> = -5.0 V, f = 100 MHz)                                                                                                                                                                                                                                                  | f <sub>T</sub>       | 100                      | -                                              | -                                           | MHz  |
| Input Capacitance (V <sub>EB</sub> = -0.5 V, f = 1.0 MHz)                                                                                                                                                                                                                                                                              | C <sub>ibo</sub>     | -                        |                                                | 650                                         | pF   |
| Output Capacitance (V <sub>CB</sub> = -3.0 V, f = 1.0 MHz)                                                                                                                                                                                                                                                                             | C <sub>obo</sub>     | -                        |                                                | 100                                         | pF   |

4. Pulsed Condition: Pulse Width = 300 μsec, Duty Cycle ≤ 2%

# NSS40400CF8T1G

## PACKAGE DIMENSIONS

### ChipFET CASE 1206A-03 ISSUE F



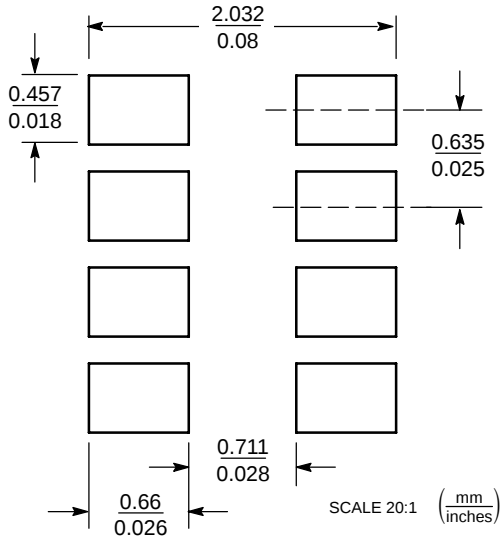
STYLE 4:  
PIN 1. COLLECTOR  
2. COLLECTOR  
3. COLLECTOR  
4. BASE  
5. EMITTER  
6. COLLECTOR  
7. COLLECTOR  
8. COLLECTOR

#### NOTES:

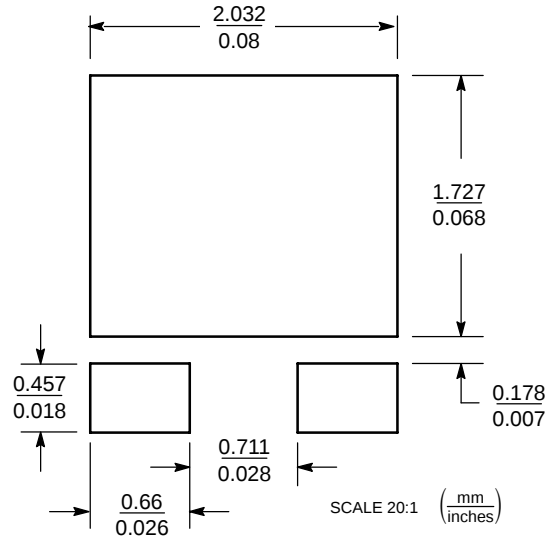
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. MOLD GATE BURRS SHALL NOT EXCEED 0.13 MM PER SIDE.
4. LEADFRAME TO MOLDED BODY OFFSET IN HORIZONTAL AND VERTICAL SHALL NOT EXCEED 0.08 MM.
5. DIMENSIONS A AND B EXCLUSIVE OF MOLD GATE BURRS.
6. NO MOLD FLASH ALLOWED ON THE TOP AND BOTTOM LEAD SURFACE.

| DIM | MILLIMETERS |      | INCHES    |       |
|-----|-------------|------|-----------|-------|
|     | MIN         | MAX  | MIN       | MAX   |
| A   | 2.95        | 3.10 | 0.116     | 0.122 |
| B   | 1.55        | 1.70 | 0.061     | 0.067 |
| C   | 1.00        | 1.10 | 0.039     | 0.043 |
| D   | 0.25        | 0.35 | 0.010     | 0.014 |
| G   | 0.65 BSC    |      | 0.025 BSC |       |
| J   | 0.10        | 0.20 | 0.004     | 0.008 |
| K   | 0.28        | 0.42 | 0.011     | 0.017 |
| L   | 0.55 BSC    |      | 0.022 BSC |       |
| M   | 5° NOM      |      | 5° NOM    |       |
| S   | 1.80        | 2.00 | 0.072     | 0.080 |

## SOLDERING FOOTPRINT\*



Basic



Style 4

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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